

isc Silicon NPN Power Transistor

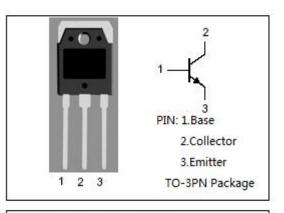
BUV48B

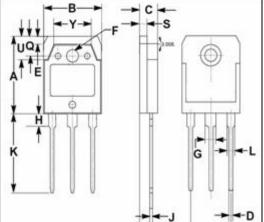
DESCRIPTION

- Collector-Emitter Sustaining Voltage-: V_{CEO(SUS)}= 600V (Min)
- High Current Capability
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

• Designed for switching and industrial applications from single and three-phase mains.





	mm	
DIM	MIN	MAX
Α	19.60	20.30
В	15.50	15.70
С	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
Н	3.20	3.40
J	0.595	0.605
Κ	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V _{сво}	Collector-Base Voltage	1200	V
V _{CEO}	Collector-Emitter Voltage	600	V
V _{EBO}	Emitter-Base Voltage	7	V
lc	Collector Current-Continuous	15	А
I _{CM}	Collector Current-Peak tp< 5ms	30	А
I _B	Base Current-Continuous	4	А
I _{BM}	Base Current-peak t _p < 5ms	20	А
Pc	Collector Power Dissipation @Tc=25°C	125	W
Tj	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT
R _{th} j-c	Thermal Resistance, Junction to Case	1.0	°C/W

isc website: www.iscsemi.com



isc Silicon NPN Power Transistor

BUV48B

ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!^{\circ}\!\!^{\circ}\!\!^{\circ}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 50mA; I _B = 0	600		V
V _{CER(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 0.5A; L= 2mH; V _{clamp} = 1200V R _{BE} = 10 Ω	1200		V
V _{CE(sat)} -1	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 1.5A		1.5	V
V _{CE (sat)-2}	Collector-Emitter Saturation Voltage	I _C = 10A; I _B = 4A		3.0	V
V _{BE} (sat)-1	Base-Emitter Saturation Voltage	I _C = 6A; I _B = 1.5A		1.5	V
V _{BE(sat)-2}	Base-Emitter Saturation Voltage	I _C = 10A; I _B = 4A		2.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 1200V ; I _B = 0		0.5	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = 600V; I _B = 0		1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0		1.0	mA

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

isc website: www.iscsemi.com